

HM62V256 Series

Product Preview

32,768-Word x 8-Bit Low Voltage Operation CMOS Static RAM



Rev. 2
Sep. 10, 1993

Features

- Low voltage operation SRAM
Operating Supply Voltage: 2.7 V to 3.6 V
- 0.8 μm Hi-CMOS process
- High speed
Access time: 85/100 ns (max)
- Low power
Standby: 0.60 μW (typ)
- Completely static memory
No clock or timing strobe required
- Directly LVTTL compatible: All inputs and outputs

Ordering Information

Type No.	Access time	Package
HM62V256LFP-8T	85 ns	450 mil
HM62V256LFP-10T	100 ns	28-pin
HM62V256LFP-8SLT	85 ns	plastic SOP
HM62V256LFP-10SLT	100 ns	(FP-28DA)
HM62V256LT-8	85 ns	8 mm x 14 mm
HM62V256LT-10	100 ns	32-pin TSOP
HM62V256LT-8SL	85 ns	(normal type)
HM62V256LT-10SL	100 ns	(TFP-32DA)

Pin Description

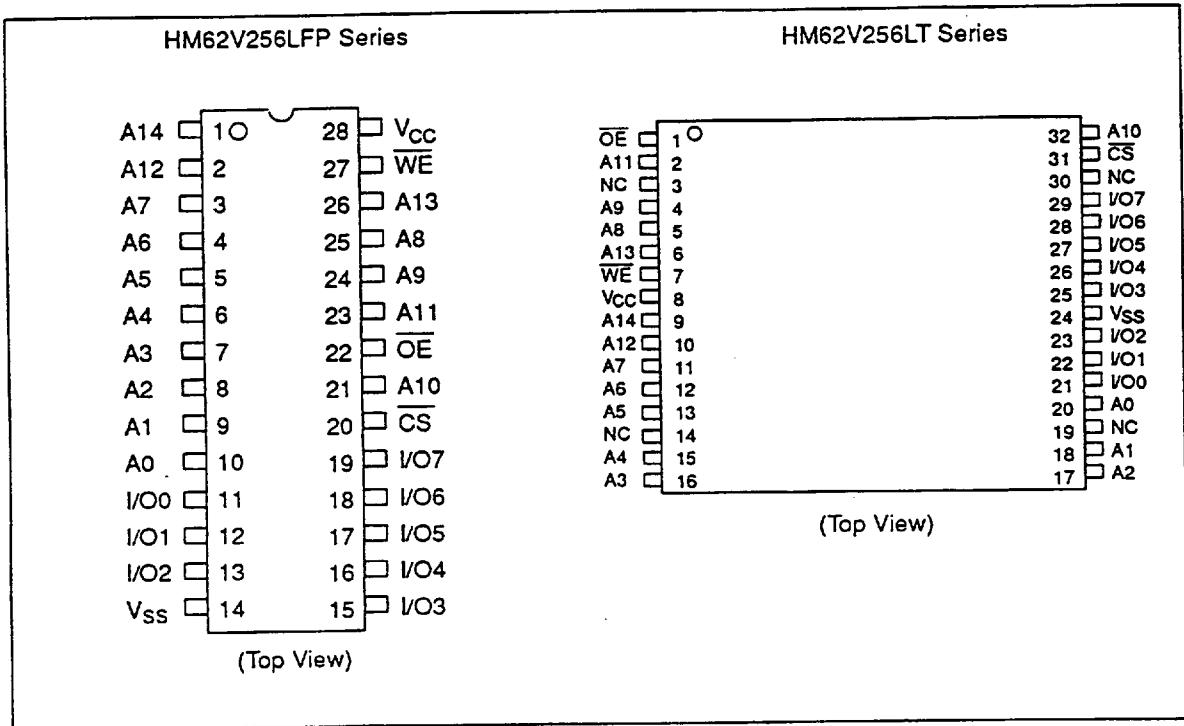
Symbol	Function
A0 – A14	Address
I/O0 – I/O7	Input/output
CS	Chip select
WE	Write enable
OE	Output enable
V _{CC}	Power supply
V _{SS}	Ground

Product preview: This document contains information on a product under development. Hitachi reserves the right to change or discontinue the product without notice.



ADE-203-136B (Z)

Pin Arrangement



Function Table

WE	CS	OE	Mode	V _{CC} current	I/O pin	Ref. cycle
X	H	X	Standby	I _{SB} , I _{SB1}	High-Z	—
H	L	H	Output disable	I _{CC}	High-Z	—
H	L	L	Read	I _{CC}	Dout	Read cycle (1)–(3)
L	L	H	Write	I _{CC}	Din	Write cycle (1)
L	L	L	Write	I _{CC}	Din	Write cycle (2)

Note: 1. X: H or L

Absolute Maximum Ratings

Item	Symbol	Value	Unit
Power supply voltage ¹	V _{CC}	–0.5 to 4.6	V
Terminal voltage ¹	V _T	–0.5 ² to +V _{CC} +0.3	V
Power dissipation	P _T	1.0	W
Operating temperature	T _{opr}	0 to +70	°C
Storage temperature	T _{stg}	–55 to +125	°C
Storage temperature under bias	T _{bias}	–10 to +85	°C

Note: 1. Relative to V_{SS}

2. V_T (min) = –3.0 V for pulse half-width ≤ 50 ns

Recommended DC Operating Conditions (Ta = 0 to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V _{CC}	2.7	3.0	3.6	V
	V _{SS}	0	0	0	V
Input high(logic 1) voltage	V _{IH}	0.7V _{CC}	—	V _{CC} +0.3	V
Input low(logic 0) voltage	V _{IL}	–0.3 ¹	—	0.2V _{CC}	V

Note: 1. V_{IL} (min) = –3.0 V for pulse half-width ≤ 50 ns

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DC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 2.7$ V to 3.6 V, $V_{SS} = 0$ V)

Parameter	Symbol	Min	Typ ^{*1}	Max	Unit	Test conditions
Input leakage current	$ I_{LI} $	—	—	1	μA	$V_{in} = V_{SS}$ to V_{CC}
Output leakage current	$ I_{LO} $	—	—	1	μA	$\overline{CS} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $WE = V_{IL}$, $V_{I/O} = V_{SS}$ to V_{CC}
Operating power supply current (DC)	I_{CCDC1}	—	—	15	mA	$\overline{CS} = V_{IL}$, others = V_{IH}/V_{IL} $I_{I/O} = 0$ mA
	I_{CCDC2}	—	—	10	mA	$\overline{CS} \geq V_{CC} - 0.2$ V, $V_{IH} \leq V_{CC} - 0.2$ V, $V_{IL} \leq 0.2$ V $I_{I/O} = 0$ mA
Operating power supply current	HM62V256-8 I_{CCAC1}	—	—	27	mA	min cycle, duty = 100 %, $I_{I/O} = 0$ mA $\overline{CS} = V_{IL}$, others = V_{IH}/V_{IL}
	HM62V256-10	—	—	24		
	I_{CCAC2}	—	—	10	mA	Cycle time ≥ 1 μs , duty = 100 % $I_{I/O} = 0$ mA, $\overline{CS} \leq 0.2$ V, $V_{IH} \geq V_{CC} - 0.2$ V, $V_{IL} \leq 0.2$ V
Standby V_{CC} current	I_{SB}	—	—	1	mA	$\overline{CS} = V_{IH}$
	I_{SB1}	—	0.2	50	μA	$V_{in} \geq 0$ V, $\overline{CS} \geq V_{CC} - 0.2$ V,
	—	—	0.2	10^{-2}	μA	
Output low voltage	V_{OL}	—	—	0.2	V	$I_{OL} = 20$ μA
Output high voltage	V_{OH}	$V_{CC} - 0.2$	—	—	V	$I_{OH} = -20$ μA

Note: 1. Typical values are at $V_{CC} = 3.0$ V, $T_a = +25^\circ\text{C}$ and not guaranteed.
2. This characteristic is guaranteed only for L-SL version.

Capacitance ($T_a = 25^\circ\text{C}$, $f = 1.0$ MHz)^{*1}

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Input capacitance	C_{in}	—	—	8	pF	$V_{in} = 0$ V
Input/output capacitance	$C_{I/O}$	—	—	10	pF	$V_{I/O} = 0$ V

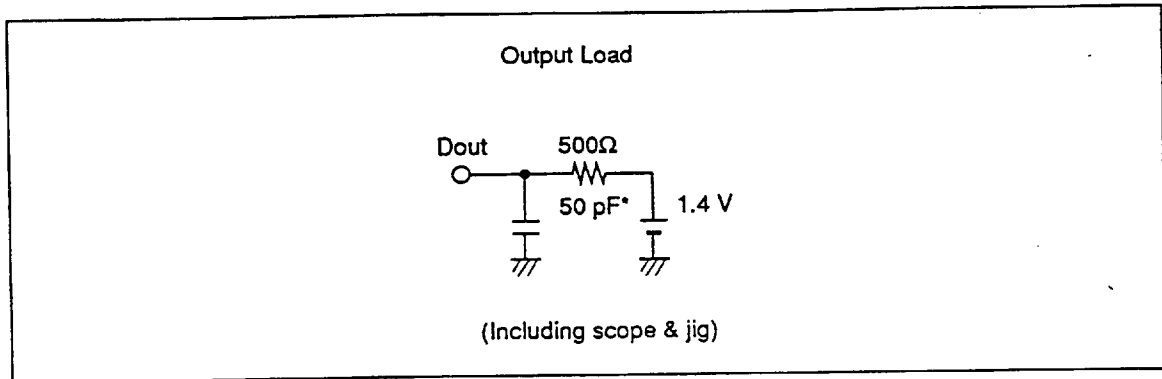
Note: 1. This parameter is sampled and not 100% tested.

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AC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 2.7$ V to 3.6 V, unless otherwise noted.)

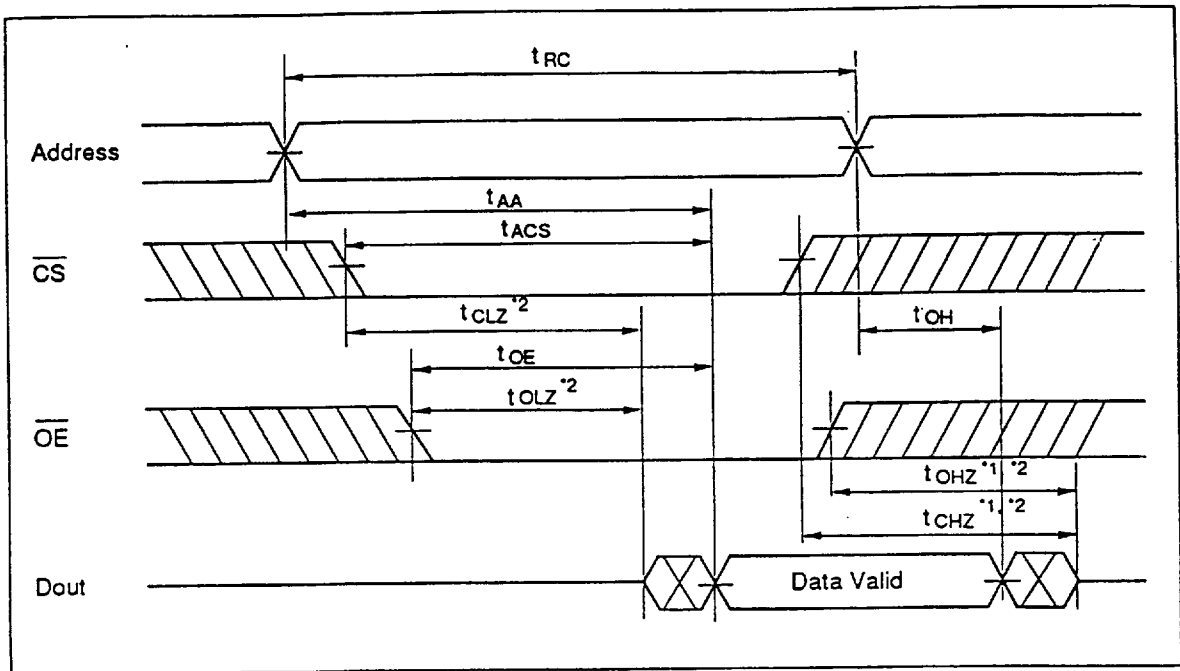
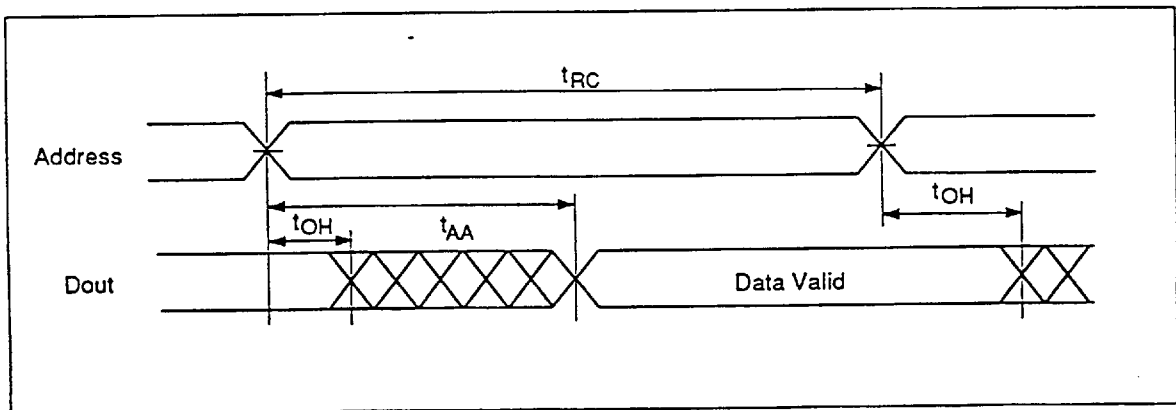
Test Conditions

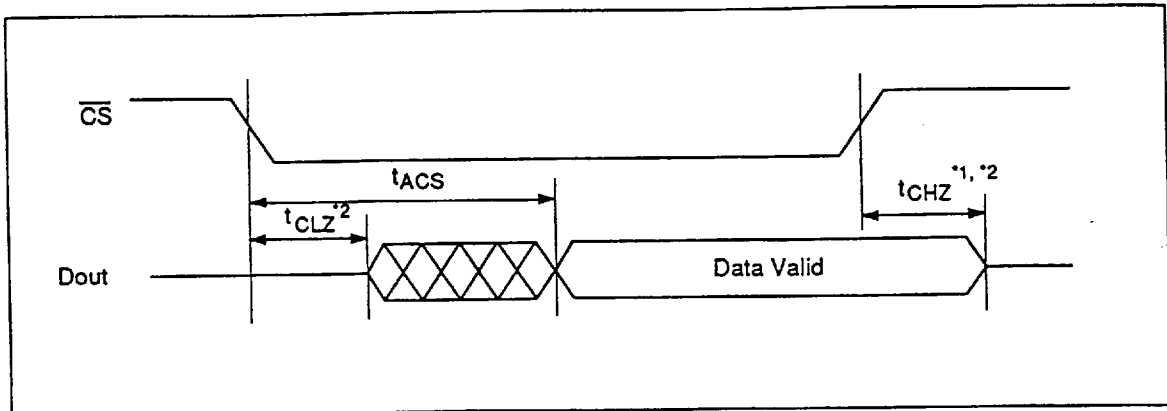
- Input pulse levels: 0.4 V to 2.4 V
- Input rise and fall times: 5 ns
- Input and output timing reference level: 1.4 V



Read Cycle

Parameter	Symbol	HM62V256-8		HM62V256-10		Unit	Notes
		Min	Max	Min	Max		
Read cycle time	t_{RC}	85	—	100	—	ns	
Address access time	t_{AA}	—	85	—	100	ns	
Chip select access time	t_{ACS}	—	85	—	100	ns	
Output enable to output valid	t_{OE}	—	45	—	50	ns	
Chip selection to output in low-Z	t_{CLZ}	10	—	10	—	ns	2
Output enable to output in low-Z	t_{OLZ}	5	—	5	—	ns	2
Chip deselection to output in high-Z	t_{CHZ}	0	30	0	35	ns	1, 2
Output disable to output in high-Z	t_{OHZ}	0	30	0	35	ns	1, 2
Output hold from address change	t_{OH}	10	—	10	—	ns	

Read Timing Waveform (1)^{*3}Read Timing Waveform (2)^{*3 *4 *6}

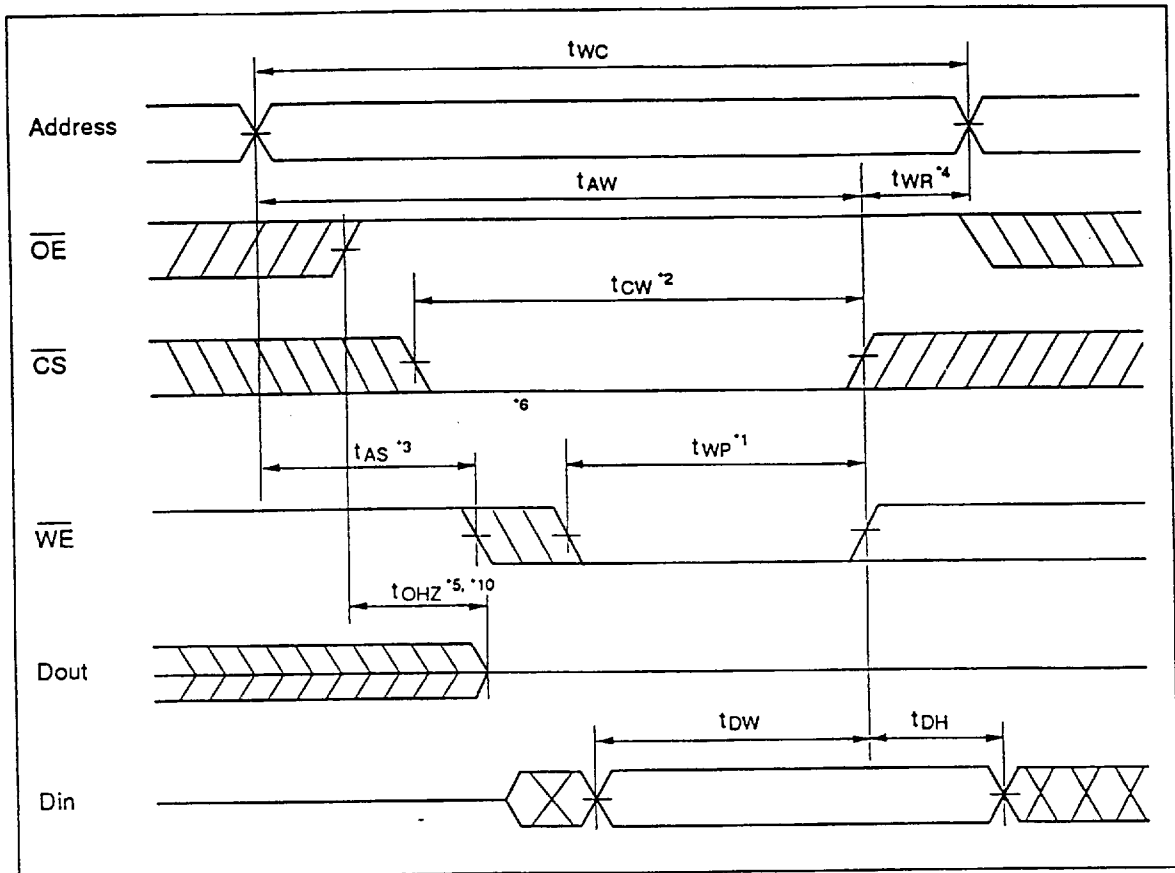
Read Timing Waveform (3)^{*3} *5 *6

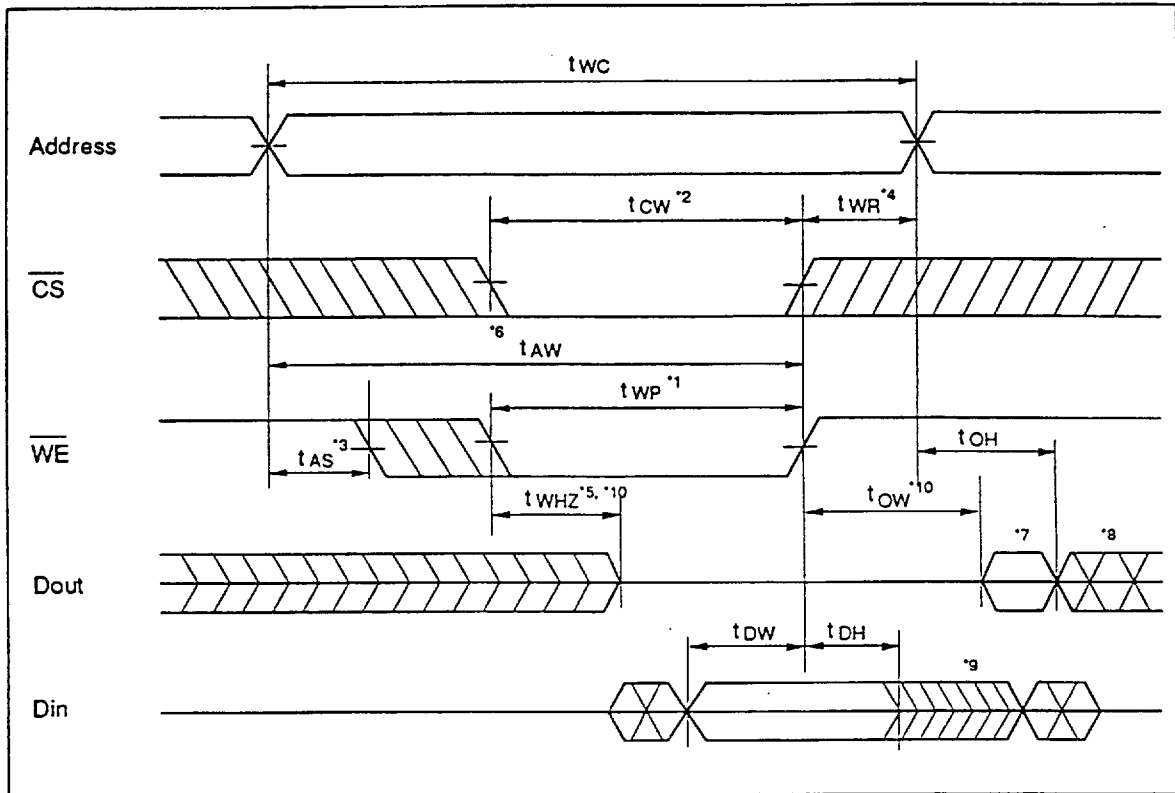
- Notes:
1. t_{CHZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
 2. This parameter is sampled and not 100 % tested.
 3. $\overline{WE}$ is high for read cycle.
 4. Device is continuously selected, $\overline{CS} = V_{IL}$
 5. Address Valid prior to or coincident with $\overline{CS}$ transition Low.
 6. $\overline{OE} = V_{IL}$

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Write cycle

Parameter	Symbol	HM62V256-8		HM62V256-10		Unit	Notes
		Min	Max	Min	Max		
Write cycle time	t_{WC}	85	—	100	—	ns	
Chip selection to end of write	t_{CW}	75	—	80	—	ns	2
Address setup time	t_{AS}	0	—	0	—	ns	3
Address valid to end of write	t_{AW}	75	—	80	—	ns	
Write pulse width	t_{WP}	55	—	60	—	ns	1
Write recovery time	t_{WR}	0	—	0	—	ns	4
Write to output in high-Z	t_{WHZ}	0	30	0	35	ns	10, 11
Data to write time overlap	t_{DW}	35	—	40	—	ns	
Data hold from write time	t_{DH}	0	—	0	—	ns	
Output active from end of write	t_{OW}	10	—	10	—	ns	10
Output disable to output in high-Z	t_{OHZ}	0	30	0	35	ns	10, 11

Write Timing Waveform (1) ($\overline{\text{OE}}$ Clock)

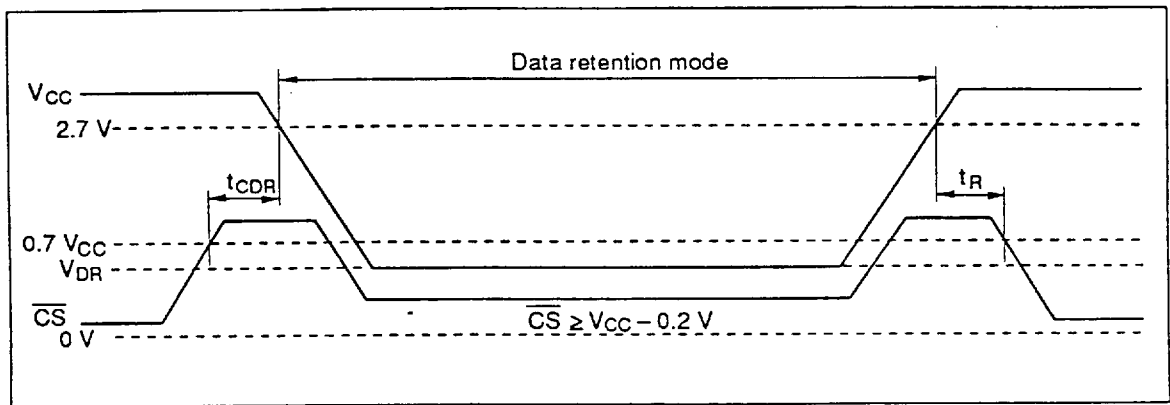
Write Timing Waveform (2) ($\overline{OE}$ Low Fixed)

- Notes:
1. A write occurs during the overlap of a low $\overline{CS}$ and a low $\overline{WE}$. A write begins at the later transition of $\overline{CS}$ going low or $\overline{WE}$ going low. A write ends at the earlier transition of $\overline{CS}$ going high or $\overline{WE}$ going high. t_{WP} is measured from the beginning of write to the end of write.
 2. t_{CW} is measured from $\overline{CS}$ going low to the end of write.
 3. t_{AS} is measured from the address valid to the beginning of write.
 4. t_{WR} is measured from the earlier of $\overline{WE}$ or $\overline{CS}$ going high to the end of write cycle.
 5. During this period, I/O pins are in the output state so that the input signals of the opposite phase to the outputs must not be applied.
 6. If the $\overline{CS}$ low transition occurs simultaneously with the $\overline{WE}$ low transition or after the $\overline{WE}$ low transition, the outputs remain in a high impedance state.
 7. D_{out} is the same phase of the write data of this write cycle.
 8. D_{out} is the read data of next address.
 9. If $\overline{CS}$ is low during this period, I/O pins are in the output state. Therefore, the input signals of the opposite phase to the output must not be applied to them.
 10. This parameter is sampled and not 100% tested.
 11. t_{OHZ} and t_{WHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.

Low V_{CC} Data Retention Characteristics ($T_a = 0$ to $+70^\circ\text{C}$)

Parameter	Symbol	Min	Typ ^{*1}	Max	Unit	Test conditions
V_{CC} for data retention	V_{DR}	2.0	—	3.6	V	$\overline{CS} \geq V_{CC} - 0.2 \text{ V}$, $V_{in} \geq 0 \text{ V}$
Data retention current	I_{CCDR}	—	—	27^{*2}	μA	$V_{CC} = 2.7 \text{ V}$, $V_{in} \geq 0 \text{ V}$ $\overline{CS} \geq V_{CC} - 0.2 \text{ V}$
		—	—	7^{*3}	ns	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	See retention waveform
Operation recovery time	t_R	t_{RC}^{*4}	—	—	ns	

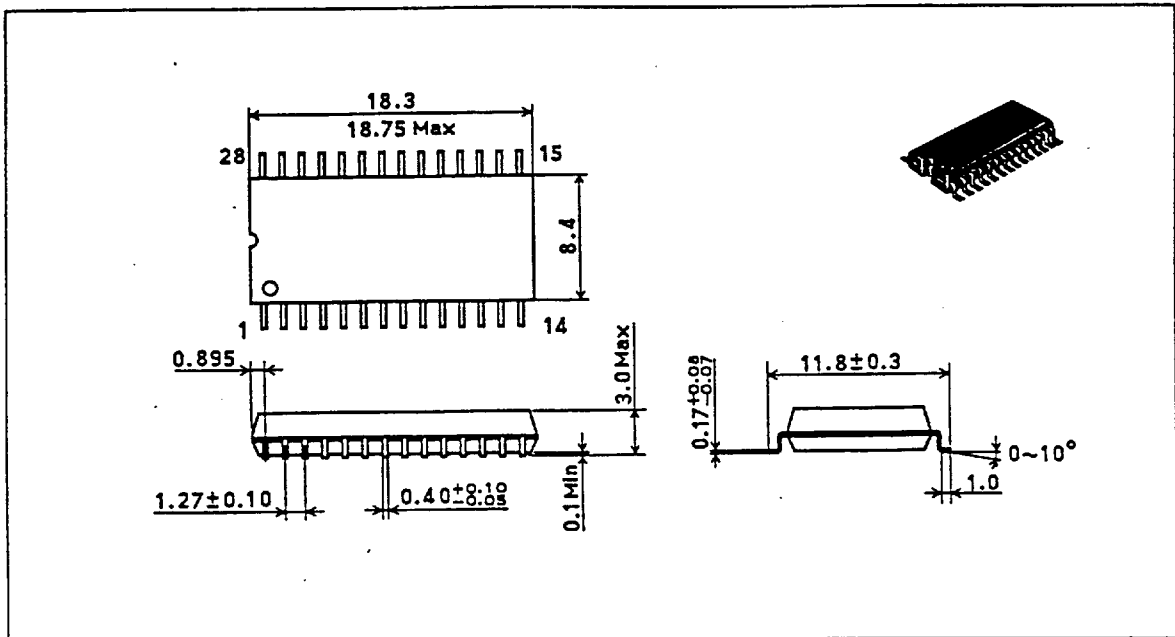
Low V_{CC} Data Retention Timing Waveform



- Notes:
1. Typical values are at $V_{CC} = 2.7 \text{ V}$, $T_a = 25^\circ\text{C}$ and not guaranteed.
 2. $18 \mu\text{A}$ max. at $T_a = 0$ to 40°C .
 3. $2.0 \mu\text{A}$ max. at $T_a = 0$ to 40°C . (only for L-SL version)
 4. t_{RC} = read cycle time.
 5. $\overline{CS}$ controls address buffer, $\overline{WE}$ buffer, $\overline{OE}$ buffer, and D_{in} buffer. If $\overline{CS}$ controls data retention mode, other input levels (address, $\overline{WE}$, $\overline{OE}$, I/O) can be in the high impedance state.

Package Dimintions

HM62V256LFP Series (FP-28DA)



HM62V256LT Series (TFP-32DA)

